



PTO/SB/08a/b (08-03)

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Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	10/603,670
				Filing Date	June 26, 2003
				First Named Inventor	Kristy A. Campbell
				Art Unit	2826
				Examiner Name	J. P. Mondt
Sheet	1	of	3	Attorney Docket Number	M4065.0457/P457-B

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (If known)			
JP	A	US 2004/0035401	2/2004	Ramachandran et al.	
JP	B	US 2003/0212724	11/2003	Ovshinsky et al.	
JP	C	US 2003/0048744	3/2003	Ovshinsky et al.	
JP	D	US 2003/0212725	11/2003	Ovshinsky et al.	
JP	E	US RE 37,259E	7/2001	Ovshinsky	
JP	F	US 3,271,591	9/1966	Ovshinsky	
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JP	H	US 3,966,317	6/1976	Wacks et al.	
JP	I	US 3,983,542	11/1976	Ovshinsky	
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JP	K	US 4,177,474	12/1979	Ovshinsky	
JP	L	US 4,267,261	5/1981	Hallman et al.	
JP	M	US 4,597,162	7/1986	Johnson et al.	
JP	N	US 4,608,296	8/1986	Keem et al.	
JP	O	US 4,637,895	1/1987	Ovshinsky et al.	
JP	P	US 4,646,266	2/1987	Ovshinsky et al.	
JP	Q	US 4,664,939	5/1987	Ovshinsky	
JP	R	US 4,668,968	5/1987	Ovshinsky et al.	
JP	S	US 4,670,763	6/1987	Ovshinsky et al.	
JP	T	US 4,673,957	6/1987	Ovshinsky et al.	
JP	U	US 4,678,679	7/1987	Ovshinsky	
JP	V	US 4,696,758	9/1987	Ovshinsky et al.	
JP	W	US 4,698,234	10/1987	Ovshinsky et al.	
JP	X	US 4,710,899	12/1987	Young et al.	
JP	Y	US 4,728,406	3/1988	Banerjee et al.	
JP	Z	US 4,737,379	4/1988	Hudgens et al.	
JP	A1	US 4,766,471	8/1988	Ovshinsky et al.	
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JP	C1	US 4,775,425	10/1988	Guha et al.	
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JP	E1	US 4,809,044	2/1989	Pryor et al.	
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Examiner: J. Mondt

[Signature]
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number	10/603,670
Filing Date	June 26, 2003
First Named Inventor	Kristy A. Campbell
Art Unit	2826
Examiner Name	J. P. Mondt
Attorney Docket Number	M4065.0457/P457-B

Sheet	2	of	3
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T1	US 5,414,271	5/1995	Ovshinsky et al.
U1	US 5,534,711	7/1996	Ovshinsky et al.
V1	US 5,534,712	7/1996	Ovshinsky et al.
W1	US 5,536,947	7/1996	Klersy et al.
X1	US 5,543,737	8/1996	Ovshinsky
Y1	US 5,591,501	1/1997	Ovshinsky et al.
Z1	US 5,596,522	1/1997	Ovshinsky et al.
A2	US 5,687,112	11/1997	Ovshinsky
B2	US 5,694,054	12/1997	Ovshinsky et al.
C2	US 5,714,768	2/1998	Ovshinsky et al.
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E2	US 5,912,839	6/1999	Ovshinsky et al.
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G2	US 6,011,757	1/2000	Ovshinsky
H2	US 6,087,674	7/2000	Ovshinsky et al.
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J2	US 6,339,544	1/2002	Chiang et al.
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L2	US 6,429,064	8/2002	Wicker
M2	US 6,437,383	8/2002	Xu
N2	US 6,462,984	10/2002	Xu et al.
O2	US 6,480,438	11/2002	Park
P2	US 6,487,113	11/2002	Park et al.
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R2	US 6,507,061	1/2003	Hudgens et al.
S2	US 6,511,862	1/2003	Hudgens et al.
T2	US 6,511,867	1/2003	Lowery et al.
U2	US 6,512,241	1/2003	Lai
V2	US 6,514,805	2/2003	Xu et al.
W2	US 6,531,373	3/2003	Gill et al.
X2	US 6,534,781	3/2003	Dennison
Y2	US 6,545,287	4/2003	Chiang
Z2	US 6,545,907	4/2003	Lowery et al.
A3	US 6,555,860	4/2003	Lowery et al.
B3	US 6,563,164	5/2003	Lowery et al.
C3	US 6,566,700	5/2003	Xu
D3	US 6,567,293	5/2003	Lowery et al.
E3	US 6,569,705	5/2003	Chiang et al.
F3	US 6,570,784	5/2003	Lowery
G3	US 6,576,921	6/2003	Lowery
H3	US 6,586,761	7/2003	Lowery
I3	US 6,589,714	7/2003	Maimon et al.
J3	US 6,590,807	7/2003	Lowery
K3	US 6,593,176	7/2003	Dennison
L3	US 6,597,009	7/2003	Wicker
M3	US 6,605,527	8/2003	Dennison et al.
N3	US 6,613,604	9/2003	Maimon et al.
O3	US 6,621,095	9/2003	Chiang et al.
P3	US 6,625,054	9/2003	Lowery et al.
Q3	US 6,642,102	11/2003	Xu

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R3	R3	US 6,646,297	11/2003	Dennison	
S3	S3	US 6,649,928	11/2003	Dennison	
T3	T3	US 6,667,900	12/2003	Lowery et al.	
U3	U3	US 6,671,710	12/2003	Ovshinsky et al.	
V3	V3	US 6,673,648	1/2004	Lowrey	
W3	W3	US 6,673,700	1/2004	Dennison et al.	
X3	X3	US 6,674,115	1/2004	Hudgens et al.	
Y3	Y3	US 6,687,427	2/2004	Ramalingam et al.	
Z3	Z3	US 6,690,026	2/2004	Peterson	
A4	A4	US 6,696,355	2/2004	Dennison	
B4	B4	US 6,687,153	2/2004	Lowery	
C4	C4	US 6,707,712	3/2004	Lowery	
D4	D4	US 6,714,954	3/2004	Ovshinsky et al.	


FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	MM-DD-YYYY			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²

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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Sheet 1 of 10

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U.S. PATENT DOCUMENTS

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AA	AA	6,388,324	05/14/2002	Kozicki et al.*	
AB	AB	US 2002/0000666	01/03/2002	Kozicki et al.*	
AC	AC	5,500,532	03/19/1996	Kozicki et al.*	
AD	AD	6,418,049	07/09/2002	Kozicki et al.*	
AE	AE	5,751,012	05/12/1998	Wolstenholme et al.*	
AF	AF	5,789,277	08/04/1998	Zahorik et al.*	
AG	AG	6,348,365	02/19/2202	Moore et al.*	
AH	AH	US 2002/0168820	11/14/2002	Kozicki et al.*	
AI	AI	6,469,364	10/22/2002	Kozicki*	
AJ	AJ	6,348,365	02/19/02	Moore et al.*	
AK	AK	6,418,049	07/09/02	Kozicki et al.*	
AL	AL	5,761,115	06/02/1998	Kozicki et al.*	
AM	AM	5,896,312	04/20/1999	Kozicki et al.*	
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AP	AP	6,635,914	10/21/2003	Kozicki et al.	

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Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
BA	BA	WO 02/21542	03/14/2002	Kozicki et al.*		
BB	BB	WO 00/48196	08/17/2000	Kozicki et al.*		
BC	BC	WO 97/48032	12/18/1997	Kozicki et al.*		
BD	BD	WO 99/28914	06/10/1999	Kozicki et al.*		

Examiner Signature	J. MONDT	Date Considered	12/07/04
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¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge ₅ As ₃₈ Te ₅₇ chalcogenide glass, Vacuum 59 (2000) 845-853. *		
	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189. *		
	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220. *		
	CD	Affifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se ₇₅ Ge _{25-x} Sb _x , Appl. Phys. A 55 (1992) 167-169. *		
	CE	Affifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe _{1-x} , Egypt, J. Phys. 17 (1986) 335-342. *		
	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag ₂ Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139. *		
	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171. *		
	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717. *		
	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089. *		
	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104. *		
	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810. *		
	CL	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557. *		
	CM	Belin, R.; Taillades, G.; Pradel, A.; Ribes, M., Ion dynamics in superionic chalcogenide glasses: complete conductivity spectra, Solid state Ionics 136-137 (2000) 1025-1029. *		
	CN	Belin, R.; Zerouale, A.; Pradel, A.; Ribes, M., Ion dynamics in the argyrodite compound Ag ₇ GeSe ₅ I: non-Arrhenius behavior and complete conductivity spectra, Solid State Ionics 143 (2001) 445-455. *		
	CO	Benmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, Phys. Rev. Lett. 73 (1994) 264-267. *		
	CP	Bernede, J.C., Influence du metal des electrodes sur les caracteristiques courant-tension des structures M-Ag ₂ Se-M, Thin solid films 70 (1980) L1-L4. *		
	CQ	Bernede, J.C., Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160. *		
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	CS	Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin solid films 131 (1985) L61-L64. *		
	CT	Bernede, J.C.; Conan, A.; Fousenan't, E.; El Bouchairi, B.; Goureaux, G., Polarized memory switching effects in Ag ₂ Se/Se/M thin film sandwiches, Thin solid films 97 (1982) 165-171. *		
	CU	Bernede, J.C.; Khellil, A.; Kettaf, M.; Conan, A., Transition from S- to N-type differential negative resistance in Al-Al ₂ O ₃ -Ag ₂ -xSe _{1+x} thin film structures, Phys. Stat. Sol. (a) 74 (1982) 217-224. *		
	CV	Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg ₄ I ₅ , Solid State Ionics 70/71 (1994) 72-76. *		
	CW	Boolchand, P., The maximum in glass transition temperature (T _g) near x=1/3 in GexSe _{1-x}		

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		Glasses, Asian Journal of Physics (2000) 9, 709-72. *	
	CX	Boalchand, P.; Georgiev, D.G.; Goodman, B., Discovery of the Intermediate Phase in Chalcogenide Glasses, J. Optoelectronics and Advanced Materials, 3 (2001), 703*	
	CY	Boalchand, P.; Selvanathan, D.; Wang, Y.; Georgiev, D.G.; Bresser, W.J., Onset of rigidity in steps in chalcogenide glasses, Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, 2001, pp. 97-132. *	
	CZ	Boalchand, P.; Enzweiler, R.N.; Tenhover, M., Structural ordering of evaporated amorphous chalcogenide alloy films: role of thermal annealing, Diffusion and Defect Data Vol. 53-54 (1987) 415-420. *	
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	CJ1	Chen, C.H.; Tai, K.L., Whisker growth induced by Ag photodoping in glassy GexSe1-x films, Appl. Phys. Lett. 37 (1980) 1075-1077. *	
	CK1	Chen, G.; Cheng, J., Role of nitrogen in the crystallization of silicon nitride-doped chalcogenide glasses, J. Am. Ceram. Soc. 82 (1999) 2934-2936. *	
	CL1	Chen, G.; Cheng, J.; Chen, W., Effect of Si3N4 on chemical durability of chalcogenide glass, J. Non-Cryst. Solids 220 (1997) 249-253. *	
	CM1	Cohen, M.H.; Neale, R.G.; Paskin, A., A model for an amorphous semiconductor memory device, J. Non-Cryst. Solids 8-10 (1972) 885-891. *	
	CN1	Croitoru, N.; Lazarescu, M.; Popescu, C.; Telnic, M.; and Vescan, L., Ohmic and non-ohmic conduction in some amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 781-786. *	
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	CP1	Davis, E.A., Semiconductors without form, Search 1 (1970) 152-155. *	
	CQ1	Deamaley, G.; Stoneham, A.M.; Morgan, D.V., Electrical phenomena in amorphous oxide films, Rep. Prog. Phys. 33 (1970) 1129-1191. *	
	CR1	Dejus, R.J.; Susman, S.; Volin, K.J.; Montague, D.G.; Price, D.L., Structure of Vitreous Ag-Ge-Se, J. Non-Cryst. Solids 143 (1992) 162-180. *	
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Examiner Signature	J. MONDT	Date Considered	12/07/04
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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete If Known	
				Application Number	10/603,670
				Filing Date	June 26, 2003
				First Named Inventor	Kristy A. Campbell
				Group Art Unit	2826
				Examiner Name	Johannes P. Mondt
				Attorney Docket Number	M4065.0457/P457-B
Sheet	10	of	10		

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